Marjorie A Olmstead

List of Publications by Year
in descending order

49 papers	1,694 citations	393982 19 h-index	276539 41 g-index
49 all docs	49 docs citations	49 times ranked	909 citing authors

#	Article	IF	Citations
1	Group III selenides: Controlling dimensionality, structure, and properties through defects and heteroepitaxial growth. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 020801.	0.9	2
2	Variation of Band Gap and Lattice Parameters of Î²â^'(Al_xGa_{1â^'x})₂O₃ Powder Produced by Solution Combustion Synthesis. Journal of the American Ceramic Society, 2016, 99, 2467-2473.	1.9	87
3	Polaronic conduction and Anderson localization in reduced strontium barium niobate. Applied Physics Letters, 2015, 107, 232901.	1.5	9
4	Site occupancy and cation binding states in reduced polycrystalline Sr_xBa_{1â^'}_xNb₂O₆. Applied Physics Letters, 2014, 104, 101607.	1.5	13
5	Sputtering-induced Co0 formation in x-ray photoelectron spectroscopy of nanocrystalline Zn1-xCoxO spinodal enrichment models. Journal of Applied Physics, 2010, 107, 103917.	1.1	7
6	Laser and electrical current induced phase transformation ofÂIn2Se3 semiconductor thin film on Si(111). Applied Physics A: Materials Science and Processing, 2008, 93, 93-98.	1.1	18
7	Heteroepitaxial growth of the intrinsic vacancy semiconductor<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msub> Si(111): Initial structure and morphology. Physical Review B, 2008, 78, .	1.1	8
8	Semiconducting chalcogenide buffer layer for oxide heteroepitaxy on Si(001). Applied Physics Letters, 2006, 88, 181903.	1.5	8
9	Influence of perovskite termination on oxide heteroepitaxy. Journal of Applied Physics, 2006, 99, 113521.	1.1	10
10	Contrast in scanning probe microscopy images of ultrathin insulator films. Applied Physics Letters, 2006, 88, 063107.	1.5	5
11	Chemical passivity of III-VI bilayer terminated Si(111). Applied Physics Letters, 2005, 87, 171906.	1.5	9
12	Intrinsic Vacancy-Induced Nanoscale Wire Structure in HeteroepitaxialGa2Se3/Si(001). Physical Review Letters, 2005, 94, 116102.	2.9	19
13	Electronic structure evolution during the growth of ultrathin insulator films on semiconductors: From interface formation to bulklikeCaF2â^•Si(111)films. Physical Review B, 2005, 72, .	1.1	11
14	Heterointerface formation of aluminum selenide with silicon: Electronic and atomic structure of Si(111):AlSe. Physical Review B, 2005, 71, .	1.1	16
15	Electronic structure of the Si(1â€‰1â€‰1):GaSe van der Waals-like surface termination. New Journal of Physics, 2005, 7, 108-108.	1.2	18
16	Atomically resolved imaging of a CaF bilayer on Si(111): Subsurface atoms and the image contrast in scanning force microscopy. Physical Review B, 2004, 69, .	1.1	13
17	Atomic structures of defects at GaSe/Si(111) heterointerfaces studied by scanning tunneling microscopy. Physical Review B, 2004, 69, .	1.1	18
18	Low-energy photoelectron diffraction structure determination of GaSe-bilayer-passivated Si(111). Physical Review B, 2001, 64, .	1.1	14

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19	Interaction of Se and GaSe with Si(111). Physical Review B, 2000, 61, 7215-7218.	1.1	39
20	Epitaxial growth of laminar crystalline silicon on CaF2. Applied Physics Letters, 2000, 77, 1289-1291.	1.5	15
21	Heteroepitaxy of Disparate Materials: From Chemisorption to Epitaxy in CaF₂/Si(111). Series on Directions in Condensed Matter Physics, 1999, , 211-266.	0.1	25
22	Altered photoemission satellites atCaF2- andSrF2-on-Si(111) interfaces. Physical Review B, 1996, 53, 1584-1593.	1.1	5
23	Growth kinetics ofCaF2/Si(111) heteroepitaxy: An x-ray photoelectron diffraction study. Physical Review B, 1995, 51, 5352-5365.	1.1	62
24	Role of Step and Terrace Nucleation in Heteroepitaxial Growth Morphology: Growth Kinetics of CaF2/Si(111). Physical Review Letters, 1995, 75, 2380-2383.	2.9	29
25	Layer-by-layer resolved core-level shifts inCaF2andSrF2on Si(111): Theory and experiment. Physical Review B, 1994, 50, 11052-11069.	1.1	27
26	Surface core-level shifts in CaF2-on-Si(111) films: Experiment and theory. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 1444.	1.6	15
27	Variable growth modes of CaF2on Si(111) determined by xâ€ray photoelectron diffraction. Applied Physics Letters, 1993, 62, 2057-2059.	1.5	29
28	CaF2-Si(111) as a model ionic-covalent system: Transition from chemisorption to epitaxy. Physical Review B, 1993, 48, 5716-5719.	1.1	23
29	Kinetic Control of CaF2 on Si(111) Growth Morphology. Materials Research Society Symposia Proceedings, 1993, 312, 207.	0.1	0
30	Local-field corrections to surface and interface core-level shifts in insulators. Physical Review B, 1992, 46, 12884-12887.	1.1	16
31	Atomic-size effects on the growth ofSrF2and (Ca,Sr)F2on Si(111). Physical Review B, 1991, 43, 7335-7338.	1.1	7
32	Role of lattice mismatch and surface chemistry in the formation of epitaxial semiconductor-insulator interfaces. Physical Review B, 1990, 41, 8420-8430.	1.1	20
33	Bonding of Se and ZnSe to the Si(100) surface. Physical Review B, 1989, 39, 12985-12988.	1.1	60
34	Semiconductor Surfaces and Interfaces Studied with Synchrotron Radiation. , 1989, , 285-334.		0
35	Electronic and Atomic Structure of GaAs Epitaxial Overlays on Si(111). Physical Review Letters, 1988, 61, 2957-2960.	2.9	15
36	Chemical Bonding and Lattice Mismatch in Semiconductorinsulator Heteroepitaxy: SrF2 on Si(111). Materials Research Society Symposia Proceedings, 1988, 116, 419.	0.1	1

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37	Electronic structure, atomic structure, and the passivated nature of the arsenic-terminated Si(111) surface. Physical Review B, 1987, 35, 3945-3951.	1.1	205
38	Photoemission study of bonding at theCaF2-on-Si(111) interface. Physical Review B, 1987, 35, 7526-7532.	1.1	162
39	Formation of the interface between GaAs and Si: Implications for GaAsâ€onâ€Si heteroepitaxy. Applied Physics Letters, 1987, 51, 523-525.	1.5	50
40	Optical properties and atomic structure of cleaved silicon and germanium (111) surfaces. Surface Science Reports, 1986, 6, 159-252.	3.8	52
41	Initial formation of the interface between a polar insulator and a nonpolar semiconductor: CaF2 on Si(111). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 1123.	1.6	89
42	Theory of the temperature dependence of Si(111)2Ã—1 surface-state optical absorption. Physical Review B, 1986, 33, 8402-8409.	1.1	18
43	Arsenic overlayer on Si(111): Removal of surface reconstruction. Physical Review B, 1986, 34, 6041-6044.	1.1	171
44	Temperature dependence of the Si and Ge (111)2Ã—1 surface-state optical absorption. Physical Review B, 1986, 33, 2564-2573.	1.1	19
45	Polarization Dependent Ge and Si (111)2x1 Surface State Optical Absorption: A Test of surface Reconstruction Models. , 1985, , 21-26.		0
46	Direct Measurement of the Polarization Dependence of Si(111)2Ã—1 Surface-State Absorption by Use of Photothermal Displacement Spectroscopy. Physical Review Letters, 1984, 52, 1148-1151.	2.9	159
47	Polarization dependence of Ge(111)2Ã—1 surface-state absorption using photothermal displacement spectroscopy: A test of surface reconstruction models. Physical Review B, 1984, 29, 7048-7050.	1.1	39
48	A novel method for the study of optical properties of surfaces. Surface Science, 1983, 132, 68-72.	0.8	18
49	A new probe of the optical properties of surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1983, 1, 751.	1.6	39